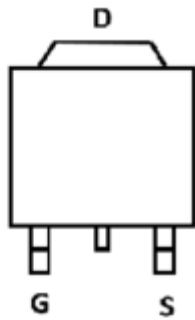
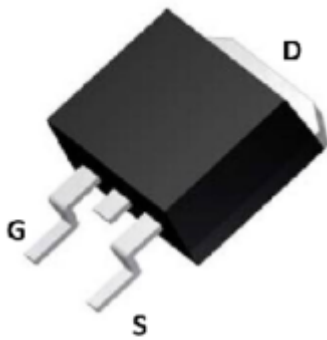
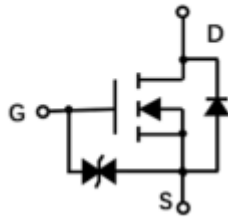


N-Channel Enhancement Mode Field Effect Transistor



TO-263



Product Summary

- V_{DS} 60V
- I_D (Silicon limited) 150A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <3.5 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <5.0 mohm
- 100% UIS Tested
- 100% ∇V_{DS} Tested
- ESD Protected up to 2.0KV(HBM)

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- Synchronous Rectification
- Battery Protection Circuit
- Motor drivers and Uninterruptible Power Supplies

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current (Silicon limited)	I_D	$T_C=25^\circ\text{C}$	150
		$T_C=100^\circ\text{C}$	95
Pulsed Drain Current ^A	I_{DM}	450	A
Avalanche energy ^B	EAS	441	mJ
Total Power Dissipation ^C	P_D	$T_C=25^\circ\text{C}$	147
		$T_C=100^\circ\text{C}$	59
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$R_{\theta JA}$	$t \leq 10S$	12	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient ^D		Steady-State	48	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.7	0.85	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB150G06AK	F2	YJB150G06AK	800	/	8000	13" reel



YJB150G06AK

■ Electrical Characteristics (T_j=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =20A		2.7	3.5	mΩ
		V _{GS} = 4.5V, I _D =20A		3.5	4.8	mΩ
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V		0.8	1.3	V
Maximum Body-Diode Continuous Current	I _S				150	A
Gate resistance	R _G	f= 1 MHz, Open drain		2.0		Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1MHZ		4650		pF
Output Capacitance	C _{oss}			850		
Reverse Transfer Capacitance	C _{rss}			65		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =25A		71		nC
Gate-Source Charge	Q _{gs}			17		
Gate-Drain Charge	Q _{gd}			10.5		
Reverse Recovery Chrage	Q _{rr}	I _F =20A, di/dt=500A/us		39.8		
Reverse Recovery Time	t _{rr}			41.6		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =30V, I _D =25A R _{GEN} =2Ω		15.9		ns
Turn-on Rise Time	t _r			55.2		
Turn-off Delay Time	t _{D(off)}			57.5		
Turn-off fall Time	t _f			91.3		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. V_{DD}=50V, R_G=25Ω, L=0.5mH, I_{AS}=42A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



■ Typical Performance Characteristics

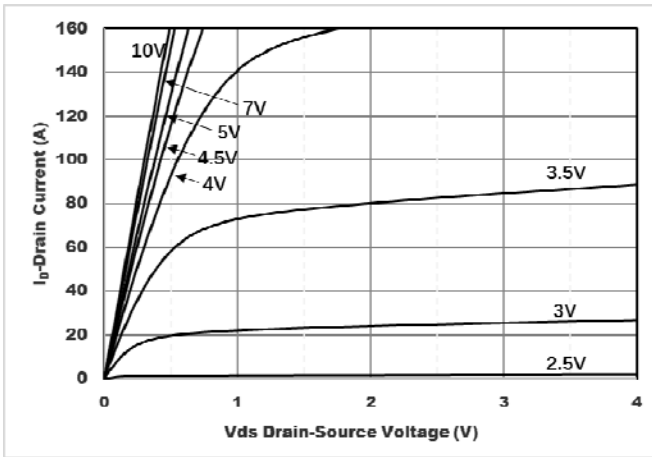


Figure1. Output Characteristics

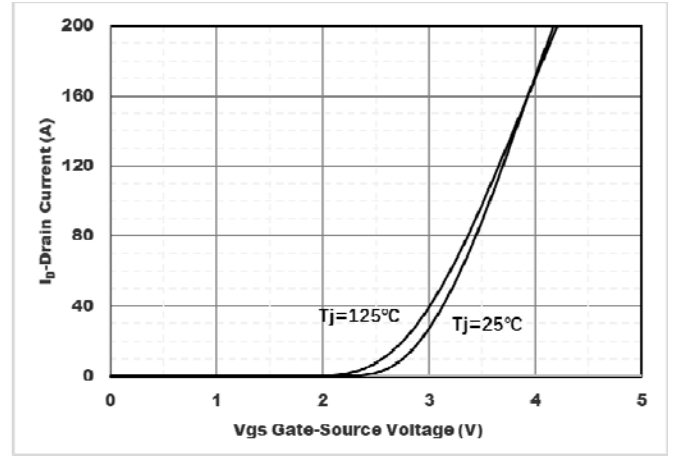


Figure2. Transfer Characteristics

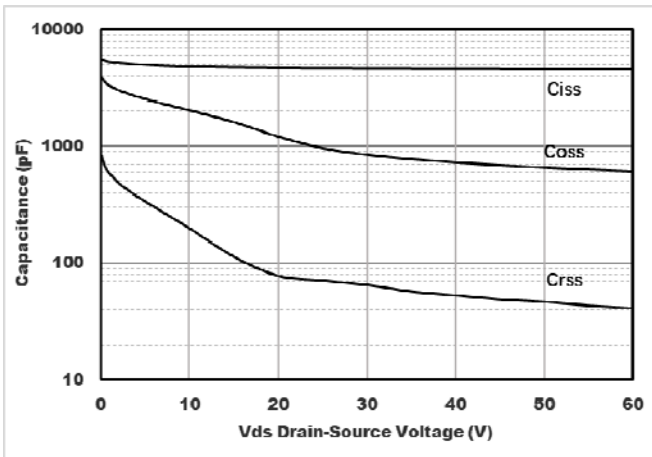


Figure3. Capacitance Characteristics

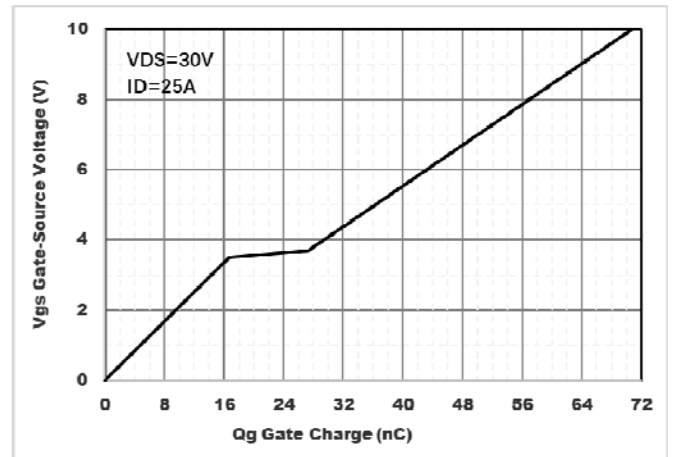


Figure4. Gate Charge

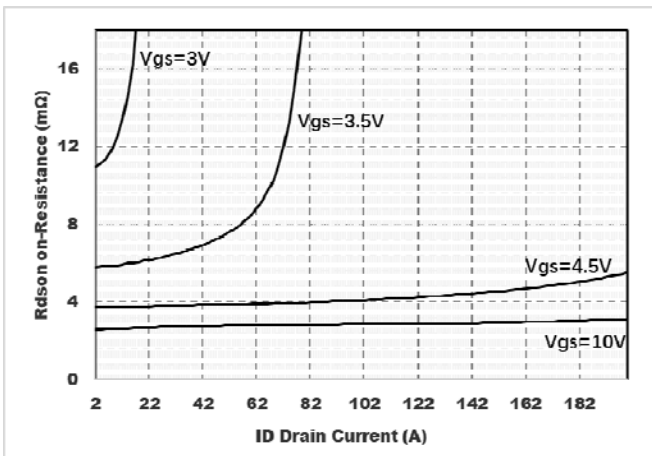


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

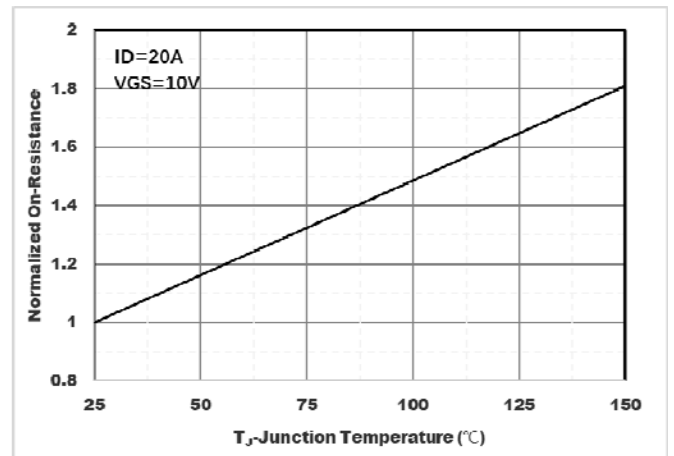


Figure6. Normalized On-Resistance



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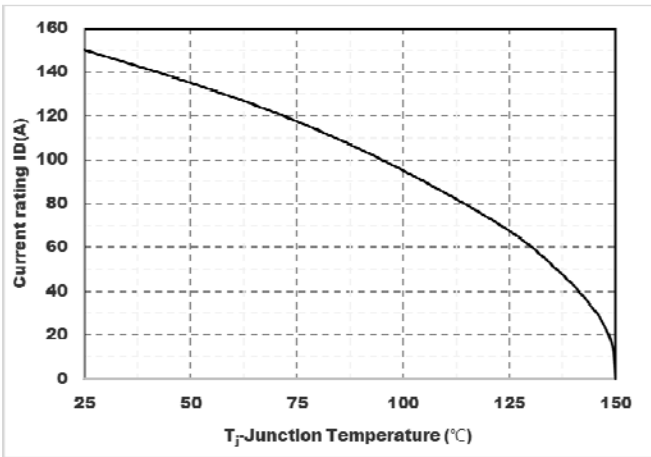


Figure7. Drain current

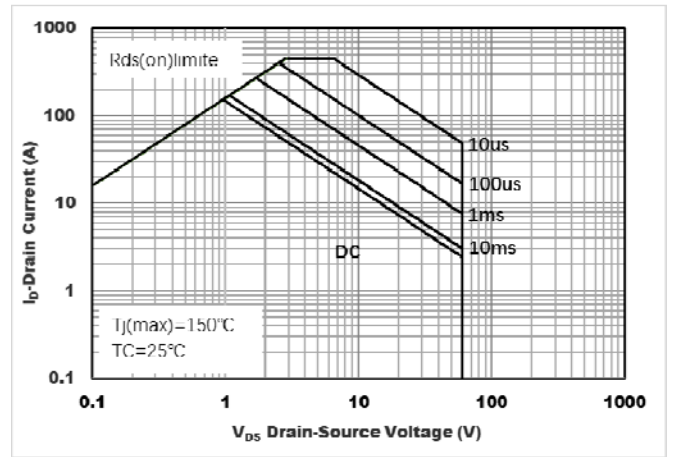


Figure8.Safe Operation Area

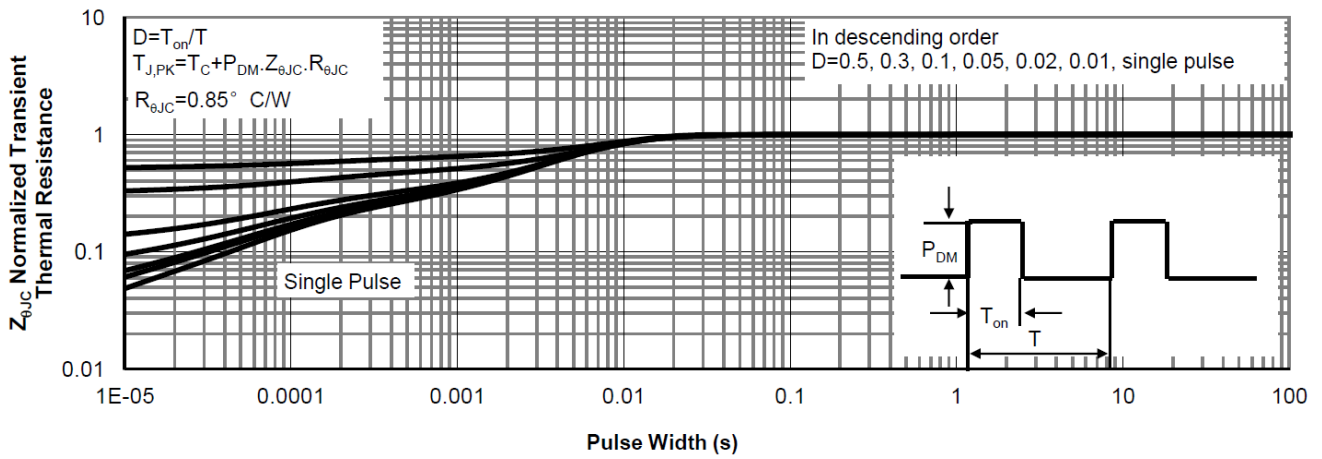
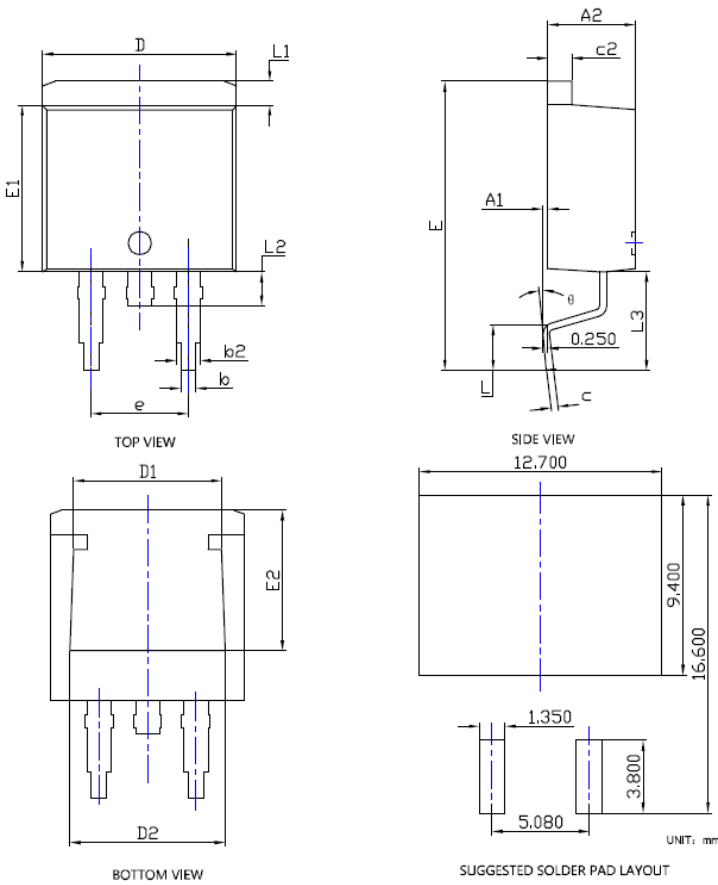


Figure9.Normalized Maximum Transient thermal impedance



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■ TO-263-HY Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.34
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
θ	0°	---	8°	0°	---	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



YJB150G06AK

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